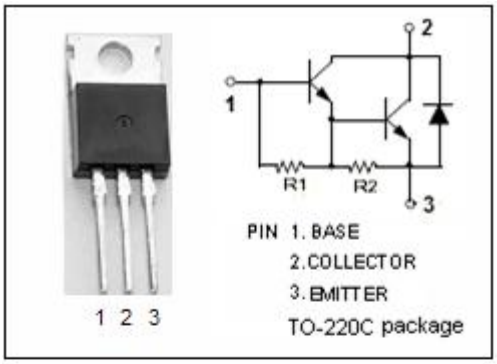
isc Silicon NPN Darlington Power Transistor 2SD930

DESCRIPTION

- High DC Current Gain
  : h_{FE}= 700(Min.)@ I_C= 1A, V_{CE}= 4V
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = 180V(Min)
- High Reliability
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

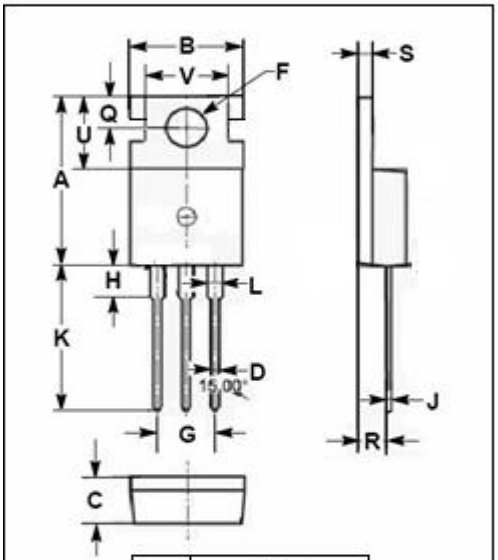


APPLICATIONS

- Color & B/W TV power supply
- Active power filter
- Series regulators
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	180	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CP}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	0.5	A
P_C	Collector Power Dissipation @T_C=25℃	30	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA, I_B= 0	180			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_B= 0	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 3mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1.5A ,I_B= 50mA			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1.5A ,I_B= 50mA			2.0	V
I_{CBO}	Collector Cutoff current	V_{CB}= 200V, I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 180V, I_B= 0			0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			3	mA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	700		20000	